

L Number	Hits	Search Text	DB	Time stamp
23	1	glue adj layer with thin adj film adj transistor\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:28
24	1	glue adj layer same thin adj film adj transistor\$1	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:29
25	63	glue adj layer same transistor\$1	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:45
26	1	etch adj stop same glue adj layer same transistor\$1	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:37
27	623	etch adj stop same (Ti or TiN)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:41
28	100	etch adj stop near3 (Ti or TiN)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:41
29	68	etch adj stop near2(Ti or TiN)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:41
30	30	etch adj stop near1(Ti or TiN)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:41
31	208	glue adj layer with TiN	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:45
32	86	glue adj layer near2 TiN	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:46
33	52	glue adj layer near1 TiN	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:48
34	1	glue adj layer near1 TiN same etch adj stop	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 13:48
-	3	AlNd and AlNdN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 15:06
-	44	thin adj film adj transistor\$1 same (neodymium or Nd) same aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 17:55
-	281	thin adj film adj transistor\$1 same hydrogenated adj amorphous adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 17:58
-	226	thin adj film adj transistor\$1 same hydrogenated adj amorphous adj silicon	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/07/18 11:21

-	10	thin adj film adj transistor\$1 same hydrogenated adj amorphous adj silicon same advantage\$1	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/07/18 13:27
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